



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

BUJ100LR

NPN power transistor

Rev. 02 — 29 July 2010

Product data sheet

1. Product profile

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) 3 leads plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability of 700 V

1.3 Applications

- Compact fluorescent lamps (CFL)
- Inverters
- Electronic lighting ballasts
- Off-line self-oscillating power supplies

1.4 Quick reference data

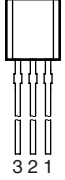
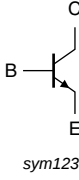
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_C	collector current	DC; see Figure 2	-	-	1	A
P_{tot}	total power dissipation	$T_{lead} \leq 25\text{ }^{\circ}\text{C}$; see Figure 1	-	-	2.1	W
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	-	700	V
Static characteristics						
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; $I_C = 0.8\text{ A}$; $T_{lead} = 25\text{ }^{\circ}\text{C}$; see Figure 8 ; see Figure 9	5	7.5	20	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 SOT54 (TO-92)	 sym123
2	C	collector		
3	E	emitter		

3. Ordering information

Table 3. Ordering information

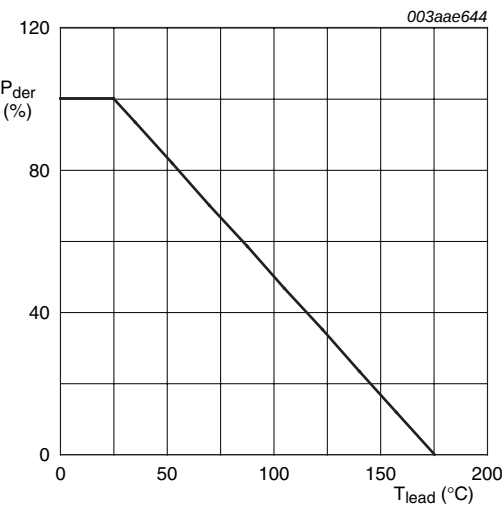
Type number	Package		
	Name	Description	Version
BUJ100LR	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4. Limiting values

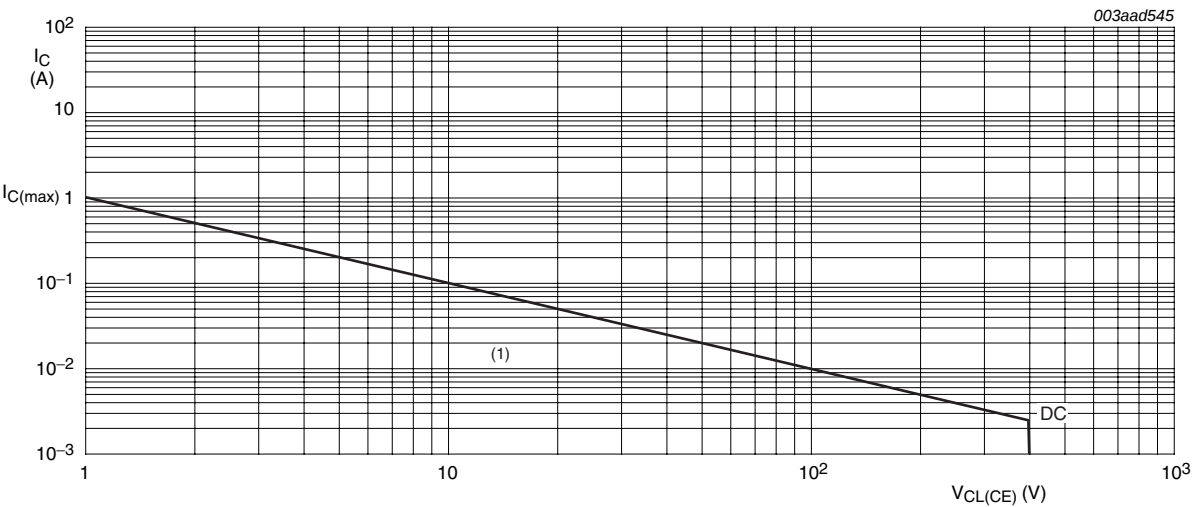
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CBO}	collector-base voltage	$I_E = 0\text{ A}$	-	700	V
V_{CEO}	collector-emitter voltage	$I_B = 0\text{ A}$	-	400	V
I_C	collector current	DC; see Figure 2	-	1	A
I_{CM}	peak collector current		-	2	A
I_B	base current	DC	-	0.5	A
I_{BM}	peak base current		-	1	A
P_{tot}	total power dissipation	$T_{lead} \leq 25\text{ °C}$; see Figure 1	-	2.1	W
T_{stg}	storage temperature		-65	150	°C
T_j	junction temperature		-	150	°C
V_{EBO}	emitter-base voltage	$I_C = 0\text{ A}$; $I(\text{Emitter}) = 10\text{ mA}$	-	9	V



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

Fig 1. Normalized total power dissipation as a function of lead temperature



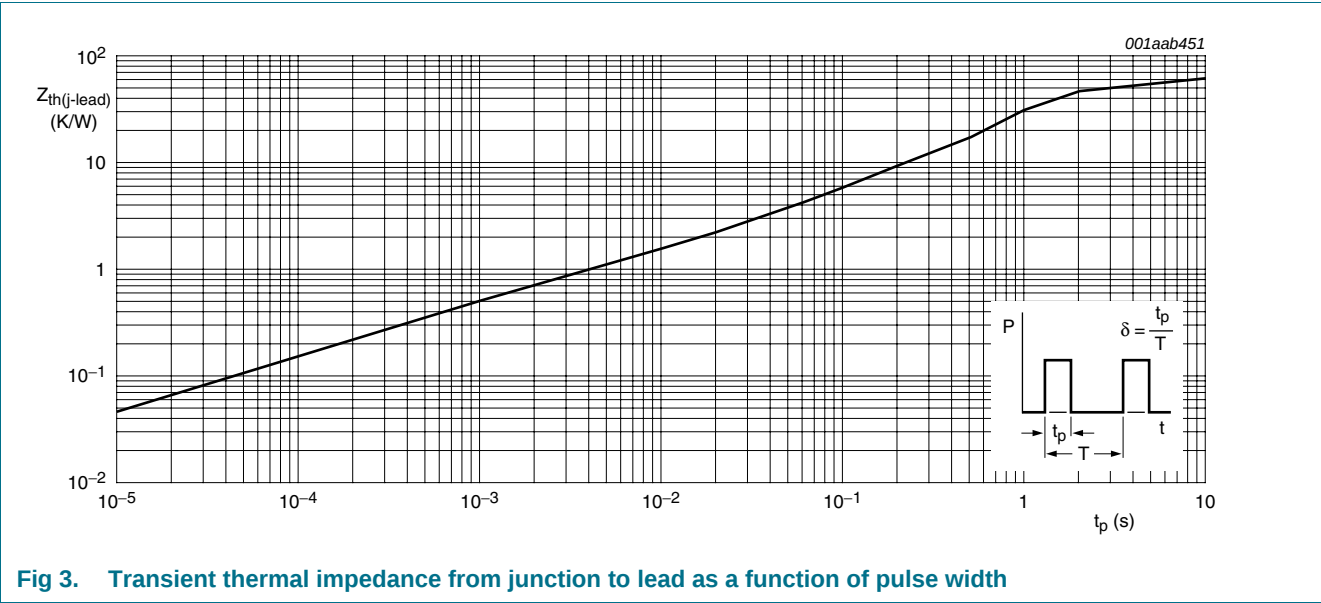
$T_{lead} \leq 25^{\circ}C$ (1) Region of permissible DC operation

Fig 2. Forward bias safe operating area

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	see Figure 3	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed-circuit board mounted; lead length 4 mm	-	150	-	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{CES}	collector-emitter cut-off current	V _{BE} = 0 V; V _{CE} = 700 V; T _j = 125 °C	-	-	5	mA
I _{EBO}	emitter-base cut-off current	V _{EB} = 9 V; I _C = 0 A; T _{lead} = 25 °C	-	-	1	mA
V _{CEOsus}	collector-emitter sustaining voltage	I _B = 0 A; I _C = 1 mA; L _C = 25 mH; T _{lead} = 25 °C; see Figure 4 ; see Figure 5	400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.25 A; I _B = 50 mA; T _{lead} = 25 °C; see Figure 6	-	0.2	0.5	V
		I _C = 0.5 A; I _B = 125 mA; T _{lead} = 25 °C; see Figure 6	-	0.3	1	V
		I _C = 0.75 A; I _B = 250 mA; T _{lead} = 25 °C; see Figure 6	-	0.4	1.5	V
V _{BEsat}	base-emitter saturation voltage	I _C = 0.25 A; I _B = 50 mA; T _{lead} = 25 °C; see Figure 7	-	-	1	V
		I _C = 0.5 A; I _B = 125 mA; T _{lead} = 25 °C; see Figure 7	-	-	1.2	V
h _{FE}	DC current gain	I _C = 0.5 mA; V _{CE} = 2 V; T _{lead} = 25 °C	12	-	-	
		I _C = 0.4 A; V _{CE} = 5 V; T _{lead} = 25 °C; see Figure 8 ; see Figure 9	10	-	30	
		I _C = 0.8 A; V _{CE} = 5 V; T _{lead} = 25 °C; see Figure 8 ; see Figure 9	5	7.5	20	
Dynamic characteristics						
t _f	fall time	I _C = 1 A; I _{Bon} = 200 mA; V _{BB} = -5 V; L _B = 1 μH; T _{lead} = 25 °C; inductive load; see Figure 10 ; see Figure 11	-	80	-	ns

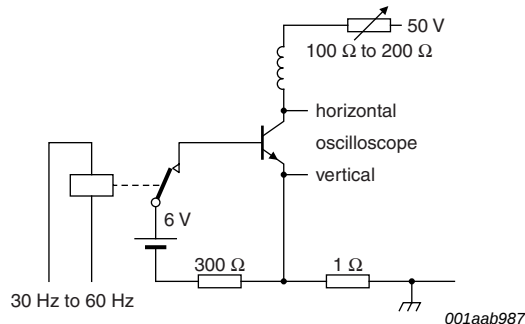


Fig 4. Test circuit for collector-emitter sustaining voltage

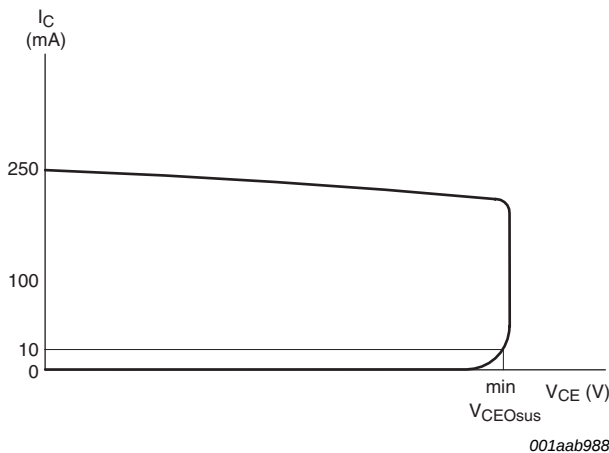


Fig 5. Oscilloscope display for collector-emitter sustaining voltage test waveform

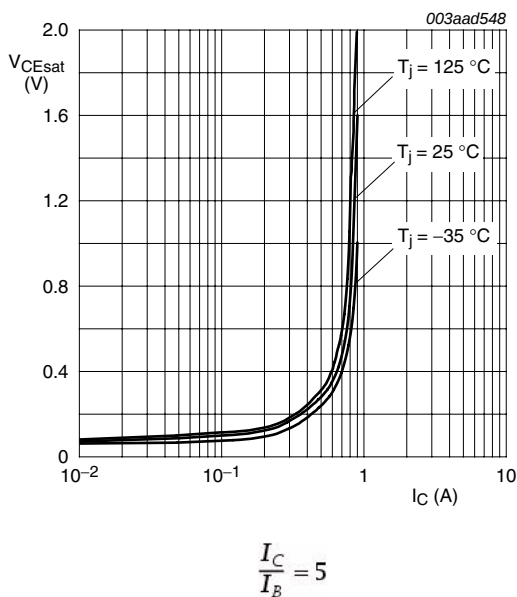


Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

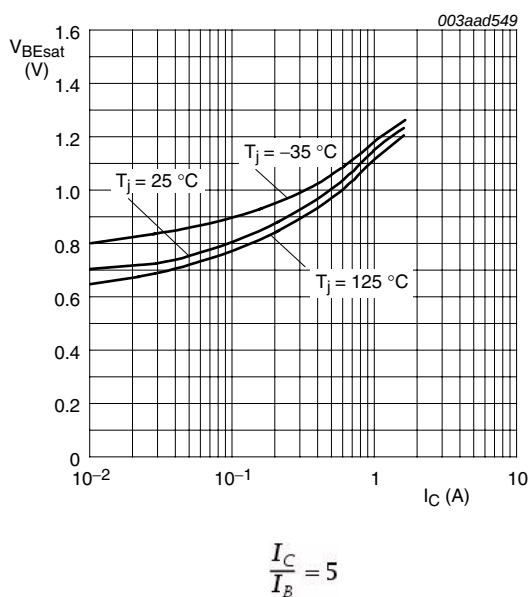
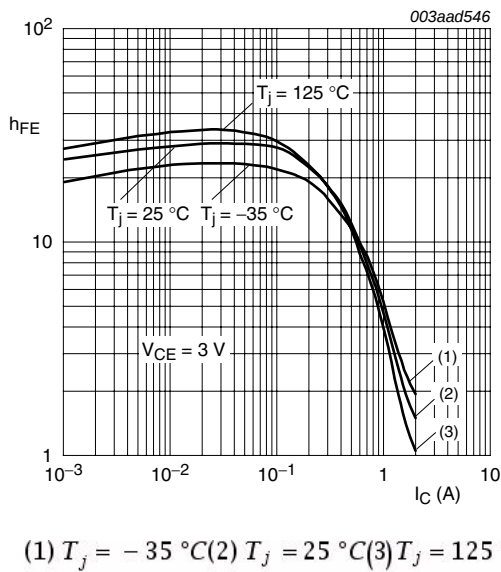
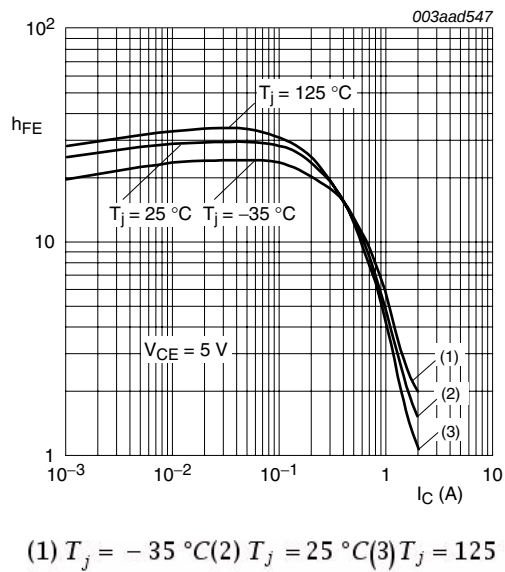


Fig 7. Base-emitter saturation voltage as a function of collector current; typical values



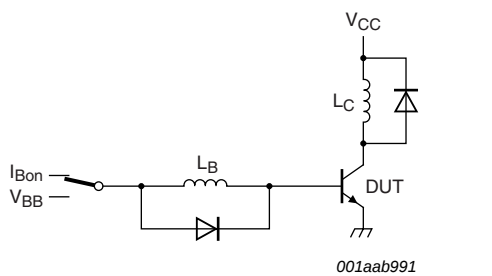
(1) $T_j = -35^\circ\text{C}$ (2) $T_j = 25^\circ\text{C}$ (3) $T_j = 125^\circ\text{C}$

Fig 8. DC current gain as a function of collector current; typical values



(1) $T_j = -35^\circ\text{C}$ (2) $T_j = 25^\circ\text{C}$ (3) $T_j = 125^\circ\text{C}$

Fig 9. DC current gain as a function of collector current; typical values



$V_{CC} = 300\text{ V}; V_{BB} = -5\text{ V}; L_C = 200\text{ }\mu\text{H}; L_B = 1\text{ }\mu\text{H}$

Fig 10. Test circuit for inductive load switching

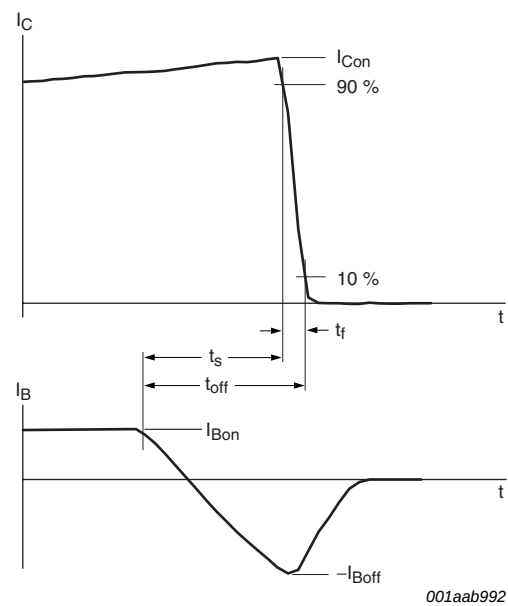


Fig 11. Switching times waveforms for inductive load

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

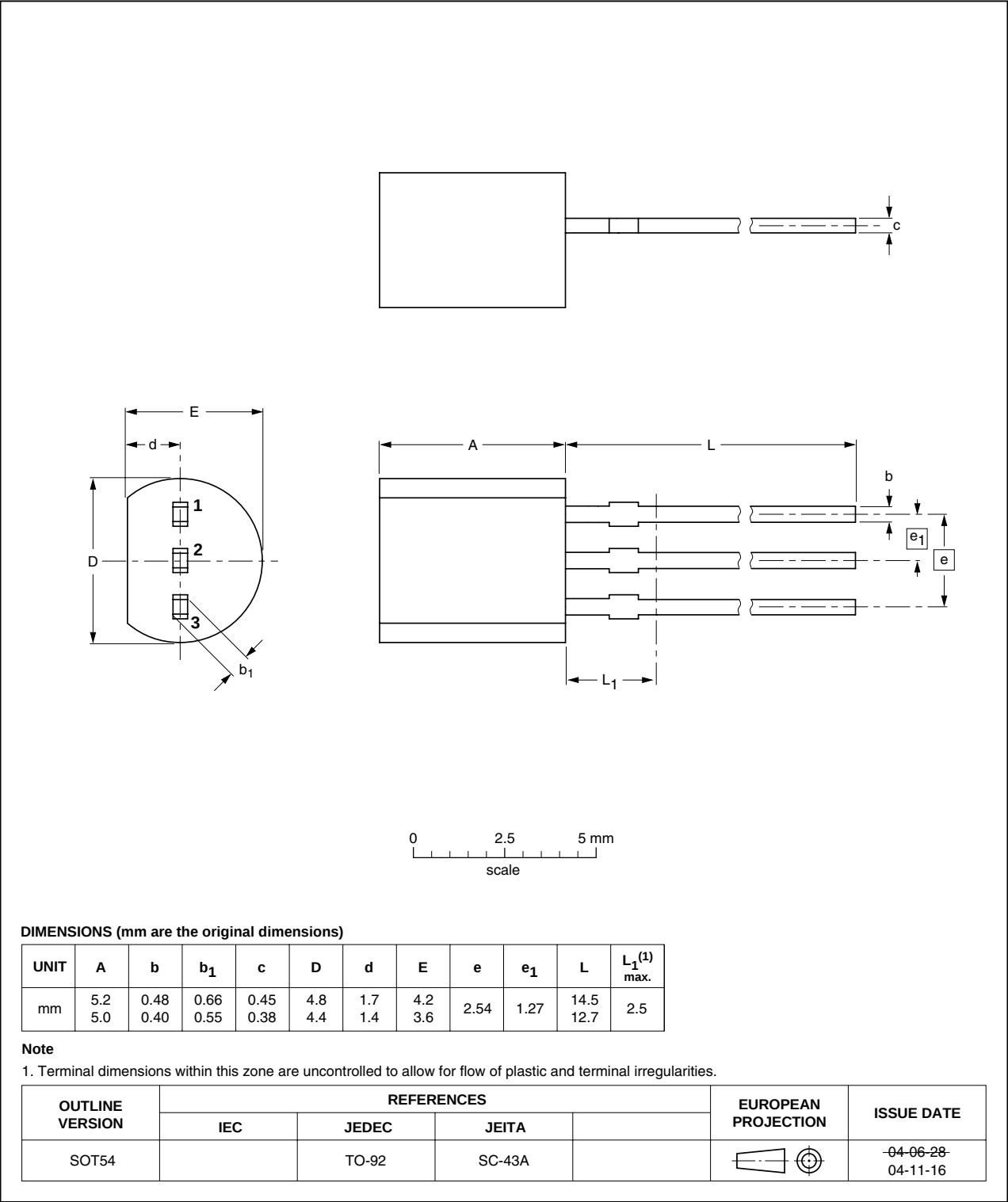


Fig 12. Package outline SOT54 (TO-92)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ100LR v.2	20100729	Product data sheet	-	BUJ100LR v.1
Modifications:	• Various changes to content.			
BUJ100LR v.1	20090812	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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